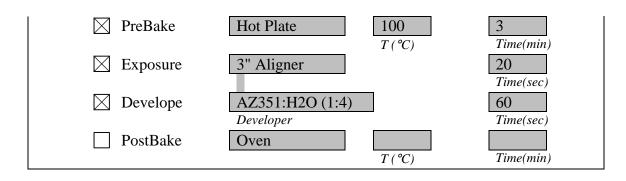
ART ONE: General descri	ption	
Process name Yael Hanein Author	Process Code hanein@ee Contact Information (Email)	05/16/00 Last Update
Deep KOH etching	Contact Information (Email)	
General description of process		

PART TWO: Details

Cleaning			
Nano-strip	10 Time (min)	BOE	1 Time (min)
\boxtimes Wet Oxidation			
			450 Thickness (nm)

Metal deposition		
Sputter sphere Evaporator	Cr Material	60 Thickness (nm)
	TiW	
	Material	Thickness (nm)
Background Pressure:	<1e-6 (<i>mTorr</i>)	

Resist Coating				
P-10 Primer	Speed1 (RPM)	Time(sec)	Speed2 (RPM)	Time(sec)
HMDS				
AZ 1512 Resist	500 Speed1 (RPM)	5 Time(sec)	3000 Speed2 (RPM)	30 Time(sec)



Etching			
BOE etchant	P (PSI)	T(°C)	10 Time(min)
	-		
comments			

Etching	_		
KOH 30% etchant	P (PSI)	0 <i>T</i> (° <i>C</i>)	250 Time(min)
comments			

Rinse and Dry

PART THREE: General Comments

To ensure good adhesion between the oxide and the metal must not use lift-off.

The developer etches the Cr so after sufficiently long developing there is no Cr left.

For the same procedure can also use TiW. In this case must etch TiW with H2O2 after lithography.

Make sure not to expose metals to Nanostrip. The nanostrip etches the metals. To have even better protection for the oxide can sputter thick layer of Au. The Au can be etched with Au etchant.